

In the Specification

At page 1, after the title insert:

CROSS REFERENCE TO RELATED APPLICATION

This patent application is a Continuation Application of U.S. Patent Application Serial No. 10/039,456 filed December 31, 2001, ^{US PAT 6,600,257} entitled "An Improved Method, Structure and Process Flow to Reduce Line-Line Capacitance with Low-K Material," naming Ying Huang and Er-Xuan Ping as inventors, which is a Divisional of U.S. Patent Application Serial No. 09/653,153 filed August 31, 2000, now U.S. Patent No. 6,531,407 which issued March 11, 2003, the disclosures of which are incorporated herein by reference.

The paragraph beginning at line 9 of page 4 has been amended as follows:

In some embodiments of the present invention, multiple levels of interconnects are formed having multiple ~~low-K~~ low-K region structures formed of one or more ~~low-K~~ low-K materials, where the one or more materials can have different insulative properties. In some multiple level embodiments in accordance with the present invention, a single type ~~low-K~~ low-K material is employed for each low-K region, while in some embodiments more than one ~~low-K~~ low-K material and or standard dielectric constant material is employed to form a dielectric region having a dielectric constant less than that which would be obtained if only such standard ~~material~~ materials are employed.